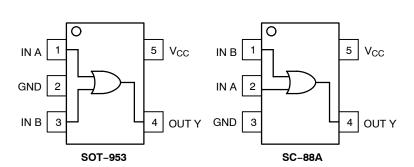
Single 2-Input OR Gate

The NL17SG32 MiniGate[™] is an advanced high-speed CMOS 2-input OR gate in ultra-small footprint.

The NL17SG32 input structures provides protection when voltages up to 4.6 V are applied.

Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: $t_{PD} = 2.4$ ns (Typ) at $V_{CC} = 3.0$ V, $C_L = 15$ pF
- Low Power Dissipation: $I_{CC} = 0.5 \ \mu A \ (Max)$ at $T_A = 25^{\circ}C$
- 4.6 V Overvoltage Tolerant (OVT) Input Pins
- Ultra-Small Packages
- These are Pb-Free and Halide-Free Devices



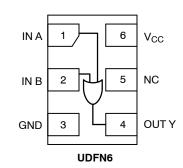


Figure 1. Pinouts (Top View)

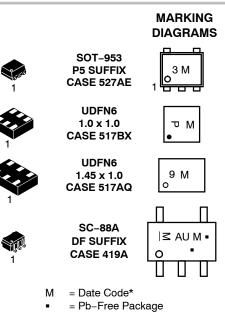


Figure 2. Logic Symbol



ON Semiconductor®

www.onsemi.com



(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT							
SOT-953 SC-88A UDFN6							
1	IN A	IN B	IN A				
2	GND	IN A	IN B				
3	IN B	GND	GND				
4	OUT Y	OUT Y	OUT Y				
5	V _{CC}	V _{CC}	NC				
6			V _{CC}				

FUNCTION TABLE

A Input	B Input	Y Output
L	L	L
L	Н	Н
Н	L	н
Н	Н	Н

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parame	ter	Value	Unit
V _{CC}	DC Supply Voltage		–0.5 to +5.5	V
V _{IN}	DC Input Voltage		-0.5 to +4.6	V
V _{OUT}	DC Output Voltage	Output at High or Low State Power–Down Mode ($V_{CC} = 0 V$)	-0.5 to V _{CC} +0.5 -0.5 to +4.6	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA
Ι _{ΟΚ}	DC Output Diode Current	V _{OUT} < GND	-20	mA
I _{OUT}	DC Output Source/Sink Current		±20	mA
I _{CC}	DC Supply Current per Supply Pin		±20	mA
I _{GND}	DC Ground Current per Ground Pin		±20	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Se	econds	260	°C
TJ	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >200	V
ILATCHUP	Latchup Performance Above	e V _{CC} and Below GND at 125℃ (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
Tested to EIA/JESD22-A114-A.
Tested to EIA/JESD22-A115-A.

4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	0.9	3.6	V
V _{IN}	Digital Input Voltage	0.0	3.6	V
V _{OUT}	Output Voltage Output at High or Low Power-Down Mode (V _{CC}		V _{CC} 3.6	V
T _A	Operating Temperature Range	-55	+125	°C
Δt / ΔV	Input Transition Rise or Fail Rate $V_{CC} = 3.3 V_{CC}$	± 0.3 V 0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

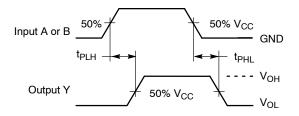
					T _A = 25°C		7⊿ -55°C to	∖ = o +125°C	
Symbol	Parameter	C	onditions	V _{CC} (V)	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input			0.9	V _{CC}		V _{CC}		V
	Voltage			1.1 to 1.3	0.7xV _{CC}		0.7xV _{CC}		1
				1.4 to 1.6	$0.65 \mathrm{xV}_{\mathrm{CC}}$		$0.65 \mathrm{xV}_{\mathrm{CC}}$		1
				1.65 to 1.95	$0.65 \mathrm{xV}_{\mathrm{CC}}$		$0.65 \mathrm{xV}_{\mathrm{CC}}$		1
				2.3 to 2.7	1.7		1.7		1
				3.0 to 3.6	2.0		2.0		1
VIL	Low-Level Input			0.9		GND		GND	V
	Voltage			1.1 to 1.3		0.3xV _{CC}		0.3xV _{CC}	1
				1.4 to 1.6		0.35xV _{CC}		0.35xV _{CC}	1
				1.65 to 1.95		0.35xV _{CC}		0.35xV _{CC}	1
				2.3 to 2.7		0.7		0.7	1
				3.0 to 3.6		0.8		0.8	1
V _{OH}	High-Level	V _{IN} =	I _{OH} = –20 μA	0.9	0.75		0.75		V
	Output Voltage	V _{IH} or V _{IL}	I _{OH} = -0.3 mA	1.1 to 1.3	$0.75 \mathrm{xV}_{\mathrm{CC}}$		$0.75 \mathrm{xV}_{\mathrm{CC}}$		1
			I _{OH} = -1.7 mA	1.4 to 1.6	$0.75 \mathrm{xV}_{\mathrm{CC}}$		$0.75 \mathrm{xV}_{\mathrm{CC}}$		1
			I _{OH} = -3.0 mA	1.65 to 1.95	Vcc-0.45		Vcc-0.45		1
			I _{OH} = -4.0 mA	2.3 to 2.7	2.0		2.0		1
			I _{OH} = -8.0 mA	3.0 to 3.6	2.48		2.48		1
V _{OL}	Low-Level	V _{IN} =	I _{OL} = 20 μA	0.9 to 3.6		0.1		0.1	V
	Output Voltage	V _{IH} or V _{IL}	I _{OL} = 1.1 mA	1.1 to 1.3		0.25xV _{CC}		0.25xV _{CC}	1
			I _{OL} = 1.7 mA	1.4 to 1.6		0.25xV _{CC}		0.25xV _{CC}	1
			I _{OL} = 3.0 mA	1.65 to 1.95		0.45		0.45	1
			I _{OL} = 4.0 mA	2.3 to 2.7		0.4		0.4	1
			I _{OL} = 8.0 mA	3.0 to 3.6		0.4		0.4	1
I _{IN}	Input Leakage Current	0 ≤	$V_{IN} \leq 3.6 V$	0 to 3.6		±0.1		±1.0	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} =	V _{CC} or GND	3.6		0.5		10.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

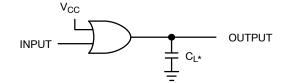
Symbol	Parameter	Test Condition	V _{CC} (V)		T _A = 25° C Min Typ Max		T⊿ -55°C to	∖ = o +125°C		
				Min			Typ Max Min Max		Min Max	
t _{PLH} ,	Propagation Delay,	$C_L = 10 \text{ pF},$	0.9	-	12.2	14.4	-	18.0	ns	
t _{PHL}	A or B to Y	$R_L = 1 M\Omega$	1.1 to 1.3	-	8.8	12.4	-	16.2		
			1.4 to 1.6	-	5.0	8.5	-	10.0		
			1.65 to 1.95	-	3.6	6.2	-	6.7		
			2.3 to 2.7	-	2.7	3.9	-	4.4		
			3.0 to 3.6	-	2.1	3.1	-	3.7		
		$C_L = 15 \text{ pF},$	0.9	-	13.0	16.0	-	18.0	ns	
	$R_{L} = 1 M\Omega$	1.1 to 1.3	-	7.8	12.0	-	16.0			
			1.4 to 1.6	-	5.9	9.3	-	11.2		
			1.65 to 1.95	-	4.5	6.9	-	7.1		
		2.3 to 2.7 - 3.0 to 3.6 -		2.3 to 2.7	-	3.0	4.4	-	5.0	
			2.4	3.4	-	3.9				
		$C_L = 30 \text{ pF},$	0.9	-	14.0	17.2	-	20.0	ns	
		R _L = 1 MΩ 1.1 to 1.3	1.1 to 1.3	-	11.0	14.1	-	17.8		
			1.4 to 1.6	-	8.0	12.1	-	15.9		
			1.65 to 1.95	-	6.0	9.2	-	9.6		
			2.3 to 2.7	-	3.9	5.7	-	6.1		
			3.0 to 3.6	-	3.0	4.4	-	4.8		
C _{IN}	Input Capacitance		0 to 3.6		3	-	-	-	pF	
C _{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	-	4	-	-	-	pF	

AC ELECTRICAL CHARACTERISTICS (Input tr = tf = 3.0 ns)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.







*Includes all probe and jig capacitance. A 1–MHz square input wave is recommended for propagation delay tests.

Figure 4. Test Circuit

ORDERING INFORMATION

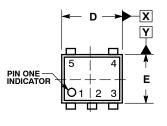
Device	Package	Shipping [†]
NL17SG32P5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel
NL17SG32DFT2G	SC-88A (Pb-Free)	3000 / Tape & Reel
NL17SG32AMUTCG	UDFN6 1.45 x 1 mm (Pb-Free)	3000 / Tape & Reel
NL17SG32CMUTCG*	UDFN6 1 x 1 mm (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

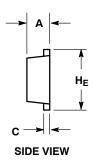
*In Development.

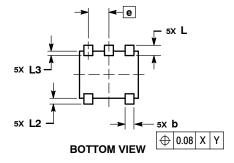
PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E



TOP VIEW

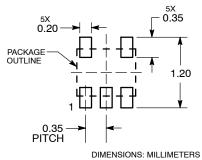




- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

TERCIT, THE THEOREM, OT G						
	MILLIMETERS					
DIM	MIN	NOM	MAX			
Α	0.34	0.37	0.40			
b	0.10	0.15	0.20			
С	0.07	0.17				
D	0.95	1.00	1.05			
Е	0.75	0.80	0.85			
е		0.35 BS	С			
HE	0.95	1.00	1.05			
L	0.175 REF					
L2	0.05	0.05 0.10 0.15				
L3			0.15			

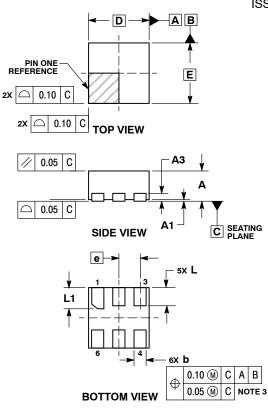
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6, 1x1, 0.35P CASE 517BX ISSUE O

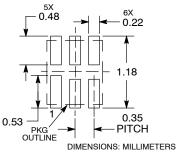


- NOTES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
 PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

 - MILLIMETERS

DIM	MIN	MAX			
Α	0.45	0.55			
A1	0.00	0.05			
A3	0.13	REF			
b	0.12	0.22			
D	1.00	BSC			
E	1.00	BSC			
е	0.35	BSC			
L	0.25	0.35			
L1	0.30	0.40			

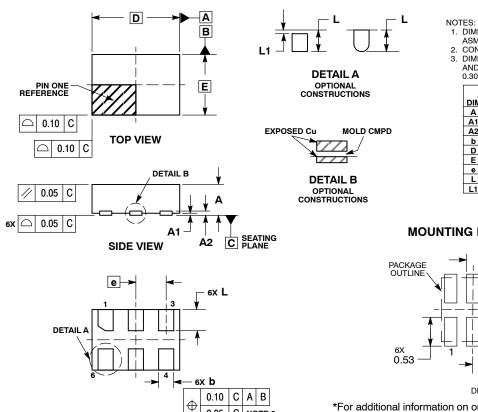
RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6, 1.45x1.0, 0.5P CASE 517AQ ISSUE O



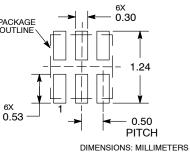
0.05 C NOTE 3

BOTTOM VIEW

NOTES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

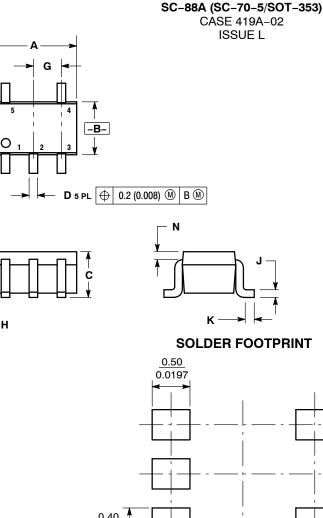
_	MILLIMETERS				
DIM	MIN	MAX			
Α	0.45	0.55			
A1	0.00	0.05			
A2	0.07 REF				
b	0.20	0.30			
D	1.45	BSC			
E	1.00	BSC			
е	0.50 BSC				
L	0.30	0.40			
L1		0.15			

MOUNTING FOOTPRINT



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS



NOTES:

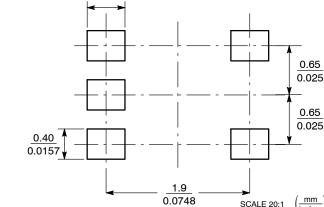
З.

DIES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 419A-01 OBSOLETE. NEW STANDARD

419A-02 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE 4

BURRS.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
Ν	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20



MiniGate is a trademark of Semiconductor Components Industries, LLC (SCILLC).

ON Semiconductor and 💷 are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. Coverage may be accessed at www.onsemi.com/site/pont/atent_Marking.pon. ON semiconductor reserves the right to make changes winnout further notice to any products nerein. ON semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights or the rights of others. ON Semiconductor products are not designed intended or suthering of the rupe ner or withing a comparent is literation are any license and any content or a particular designed during or a validated for each customer designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

Phone: 421 33 790 2910

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

S

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: <u>NL17SG32DFT2G</u> NL17SG32P5T5G